

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently amended) A method of fabricating a semiconductor device including a crystallized active layer comprising the steps of:

providing a substrate;

depositing an amorphous silicon layer on said substrate;

depositing a metal layer of Ni or Pd for inducing low temperature crystallization of amorphous silicon on at least a portion of said amorphous silicon layer by sputtering while heating said substrate to a temperature that allows at least a portion of the deposited metal to react with the amorphous silicon to form an oxidation-stable metal silicide film; and

conducting a thermal treatment of said substrate so that said amorphous silicon layer is crystallized by metal induced lateral crystallization (MILC) propagating from the portion covered by said metal layer.

2. (Canceled).

3. (Original) The method according to Claim 1, wherein the substrate is heated at a temperature in a range of 200-700°C.

4. (Original) The method according to Claim 1, wherein said metal layer is deposited using at least one of sputtering, heating evaporation, PECVD and CVD.

5. (Original) The method according to Claim 1, wherein the substrate is heated by using a heat conduction or a heat radiation method.

6. (Original) The method according to Claim 1, wherein a portion of said metal layer contacting with said amorphous silicon layer forms a metal silicide.

7. (Original) The method according to Claim 6, wherein other portions of said metal layer remain in the state of metal and further comprising a step of removing the remaining metal layer by etching.

8. (Previously presented) The method according to Claim 1, wherein at least a portion of said amorphous silicon layer is crystallized by metal induced lateral crystallization during the process of heating the substrate while depositing the metal layer.

9. (Canceled).

10. (Original) The method according to Claim 1, wherein the step of heating the substrate while depositing the metal layer comprises the steps of:

forming an insulation layer on said substrate and said amorphous silicon layer;

removing a portion of said insulation layer to expose a portion of said amorphous silicon layer; and

depositing said metal layer on the exposed surface of said amorphous silicon layer while heating said substrate.

11-17. (Canceled).